WHAT IS CLAIMED IS:

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2 (a) disposing a capacitor plate above a wafer surface on which electrostatic charges are to be scanned; 3 using a movable probe to measure voltages at various locations at the capacitor plate; 4 (b) 5 (c) collecting the measured voltage distribution; and 6 (d) examining the collected voltage distribution to identify areas on the wafer surface correspondingly to high electrostatic charge density. 7 2. 1 The method for detecting electrostatic charges on a wafer surface according to claim 1. 2 wherein the wafer contains a dielectric layer at its outmost surface. 1 3. The method for detecting electrostatic charges on a wafer surface according to claim 2, wherein the dielectric layer is an oxide layer. 2 4. 1 The method for detecting electrostatic charges on a wafer surface according to claim 1. wherein the method is performed following a cleansing step using pure water or de-ionized 2 3 water to remove particles or other impurities on the wafer surface. The method for detecting electrostatic charges on a wafer surface according to claim 1, 1 5. 2 wherein the capacitor plate is structured such that it can be moved both vertically and Liauh: WB88116\WINBOND-88-116.DC 10

A method for detecting electrostatic charges on a wafer surface, comprising the steps of:

horizontally above the wafer surface. 3 6. 1 The method for detecting electrostatic charges on a wafer surface according to claim 1, 2 wherein the capacitor plate is made of a plurality of capacitor sub-plates electrically insulated from each other. 3 7. 1 A method for detecting electrostatic charges on a wafer surface, comprising the steps of: 2 (a) disposing a capacitor plate above a wafer surface on which electrostatic charges are 3 to be scanned; (b) attaching a probe on the capacitor plate; 4 moving the capacitor plate horizontally above the wafer surface so as to allow the (c) 5 6 probe to measure voltages at various locations above the wafer surface; (d) collecting the measured voltage distribution; and 7 examining the collected voltage distribution to identify areas on the wafer surface (e) 8 correspondingly to high electrostatic charge density. 9 1 - 8. The method for detecting electrostatic charges on a wafer surface according to claim 7, 2 wherein the wafer contains a dielectric layer at its outmost surface. 9. The method for detecting electrostatic charges on a wafer surface according to claim 8, 1 2 wherein the dielectric layer is an oxide layer.

- The method for detecting electrostatic charges on a wafer surface according to claim 7, wherein the method is performed following a cleansing step using pure water or de-ionized water to remove particles or other impurities on the wafer surface.
- The method for detecting electrostatic charges on a wafer surface according to claim 7, wherein the capacitor plate is structured such that it can be moved both vertically and horizontally above the wafer surface.
- 1 12. An apparatus method for detecting electrostatic charges on a wafer surface, comprising the steps of:
- movable capacitor plate to be placed above a wafer surface on which electrostatic charges are to be scanned;
- 5 (b) a movable probe to measure voltages at various locations at the capacitor plate; and
- 6 (c) a recorder to collect and record the measured voltage distribution.
- 1 13. The apparatus for detecting electrostatic charges on a wafer surface according to claim 12, 2 wherein the wafer contains a dielectric layer at its outmost surface.
- 1 14. The apparatus for detecting electrostatic charges on a wafer surface according to claim 13, 2 wherein the dielectric layer is an oxide layer.

- 1 15. The apparatus for detecting electrostatic charges on a wafer surface according to claim 12,
- which is to be performed following a cleansing step using pure water or de-ionized water to
- remove particles or other impurities on the wafer surface.
- 1 16 The apparatus for detecting electrostatic charges on a wafer surface according to claim 12,
- wherein the capacitor plate is structured such that it can be moved both vertically and
- 3 horizontally above the wafer surface.
- 1 17. The apparatus for detecting electrostatic charges on a wafer surface according to claim 12,
- wherein the capacitor plate is made of a plurality of capacitor sub-plates electrically
- 3 insulated from each other.